



<b>LIST OF REFERENCES CITED BY APPLICANT</b> <i>(Use several sheets if necessary)</i>					ATTY. DOCKET NO.:		APPLICATION NO.:	
					4717-10000		10/784,016	
					APPLICANT:			
					Bruno GHYSELEN et al.			
					FILING DATE:		GROUP:	
					February 20, 2004		2811	

U.S. PATENT DOCUMENTS							
*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
TT	AA	5,461,243	10/1995	Ek et al.	257	190	
TT	AB	6,352,942 B1	3/2002	Luan et al.	438	770	
TT	AC	6,100,166	8/2000	Sakaguchi et al.	438	455	
	AD						
	AE						
	AF						
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	AI						

FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION
							YES NO
	AJ						
	AK						
	AL						

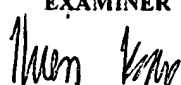
  

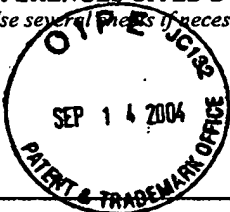
OTHER REFERENCES <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>		
TT	AM	B. Holländer et al., "Strain relaxation of pseudomorphic Si <sub>x</sub> Ge <sub>1-x</sub> /Si(100) heterostructures after hydrogen or helium ion implantation for virtual substrate fabrication", Nuclear Instruments and Methods in Physics Research B 175-177 (2001) 357-367 (2001)
TT	AN	K.D. Hobart et al. "Complaint Substrates: A Comparative Study of the Relaxation Mechanisms of Strained Films Bonded to High and Low Viscosity Oxides", Electronic Materials, Vol. 29, No. 7, pp. 897-900 (2000)
TT	AO	Friedrich Schäffler, "High-mobility Si and Ge structures", Semicond. Sci. Technol., Vol. 12, pp.1515-1548 (1997)
TT	AP	Q. Y. Tong et al "Extracts of "Semi-conductor on wafer bonding", Science and Technology, Interscience Technology, Wiley Interscience publication, Johnson Wiley & Sons, Inc.
TT	AQ	J.P. Collinge, "Silicon-on-insulator technology", Materials to VLSI, 2nd Edition", Kluwer Academic Publisher, pp. 50-51.

<b>EXAMINER</b> 	<b>DATE CONSIDERED</b> 03/09/2005
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\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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<b>U.S. PATENT DOCUMENTS</b>								
*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE	
TT	AA	5,882,987	3/1999	Sirikrishnan	438	458		
TT	AB	2002/0072130 A1	6/2002	Cheng et al.	438	10		
TT	AC	2002/0168864 A1	11/2002	Cheng et al.	438	725		
TT	AD	2002/0146892 A1	10/2002	Notsu et al.	438	455		
TT	AE	2003/0013305 A1	1/2003	Sugii et al.	438	689		
	AF							
	AG							
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<b>FOREIGN PATENT DOCUMENTS</b>								
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
TT	AJ	EP 1 248 294 A2	10/2002	Europe			X	
TT	AK	WO 99/53539	10/1999	PCT			X	
TT	AL	WO/0243153A1 (w/English Abstract)	5/2002	PCT			X	
	AM						X	
	AN						X	
	AO							
<b>OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc.)</b>								
TT	AP	T. Tezuka et al., XP001109835, <b>High-Performance Strained Si-on-Insulator MOSFETs by Novel Fabrication Processes Utilizing Ge-Condensation Technique</b> , Symposium On VLSI Tech., Digest of Technical Papers. Honolulu, NY:IEEE US, pp. 96-97 (2002)						
TT	AQ	S. Mantl et al., "Strain relaxation of epitaxial SGe layers on Si(100) improved by hydrogen implantation" Nuclear Instruments and Methods in Physics Research , Vol. 147, No. 1-4, pp. 29-34 (1999)						
EXAMINER					DATE CONSIDERED			
					03/10/2005			
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<b>U.S. PATENT DOCUMENTS</b>							
*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
TT	AA	6,059,895	5/2000	Chu et al.	148	33.1	
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	AC						
	AD						
<b>FOREIGN PATENT DOCUMENTS</b>							
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
	AE						
	AF						
<b>OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc.)</b>							
	AG						
	AH						
EXAMINER  <div style="font-family: cursive; font-size: 1.2em;">Thain Kane</div>				DATE CONSIDERED  <div style="font-family: cursive; font-size: 1.2em;">03/09/2005</div>			
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